

Process Optimization of Copper Antimony Sulfide Thin Films via Chemical Bath Deposition for High-Performance Photovoltaic Applications.

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INTRODUCTION & AIM

Key Advantages

- Direct band gap 1.5 eV (ideal for solar spectrum absorption)
- High absorption coefficient $> 10^5 \text{ cm}^{-1}$ in the visible range
- Non-toxic and environmentally friendly

Current Challenges

- Poor charge carrier transport
- High defect density
- Rapid electron-hole recombination

Research Approach

Various strategies have been explored to address these limitations

This study

- Uses Chemical Bath Deposition (CBD) technique
- Focus on optimization of the deposition bath parameters
- Aimed at achieving the best film quality and device performance

METHOD

Stage 01

Substrate Cleaning

TiO₂ Layer Coating

Chemical Bath Preparation of CuSbS₂

Stage 02

Dipping Process Optimization Process

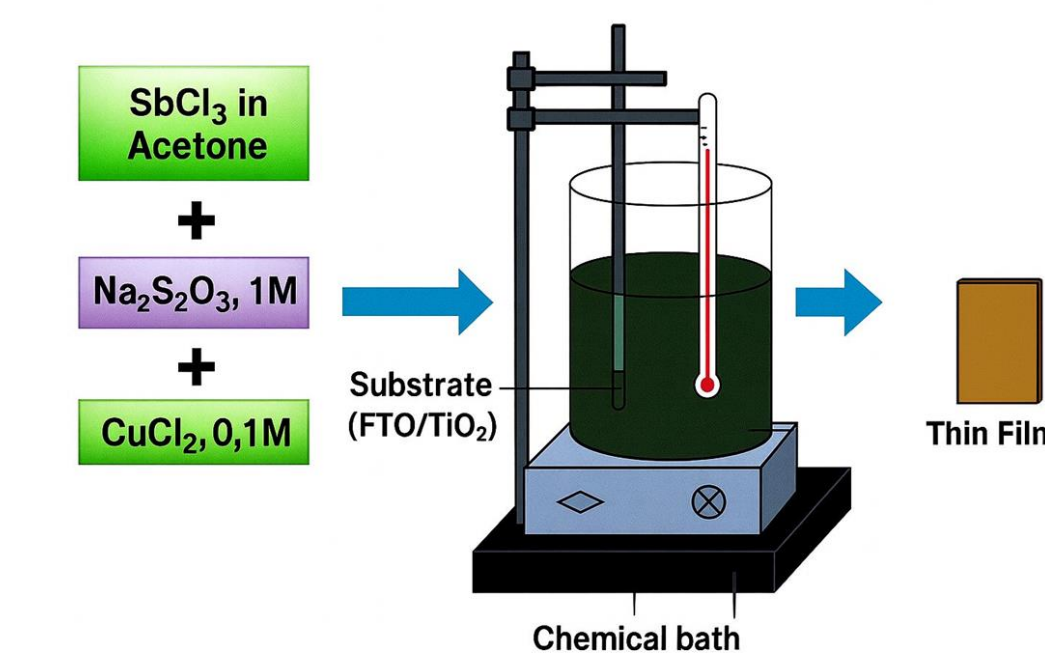


Figure 01 : Chemical Bath Process

RESULTS & DISCUSSION

Fixed Conditions

Bath temperature kept constant
CuCl₂ concentration kept constant

Variable Parameter

Only the dipping time was changed during the experiment

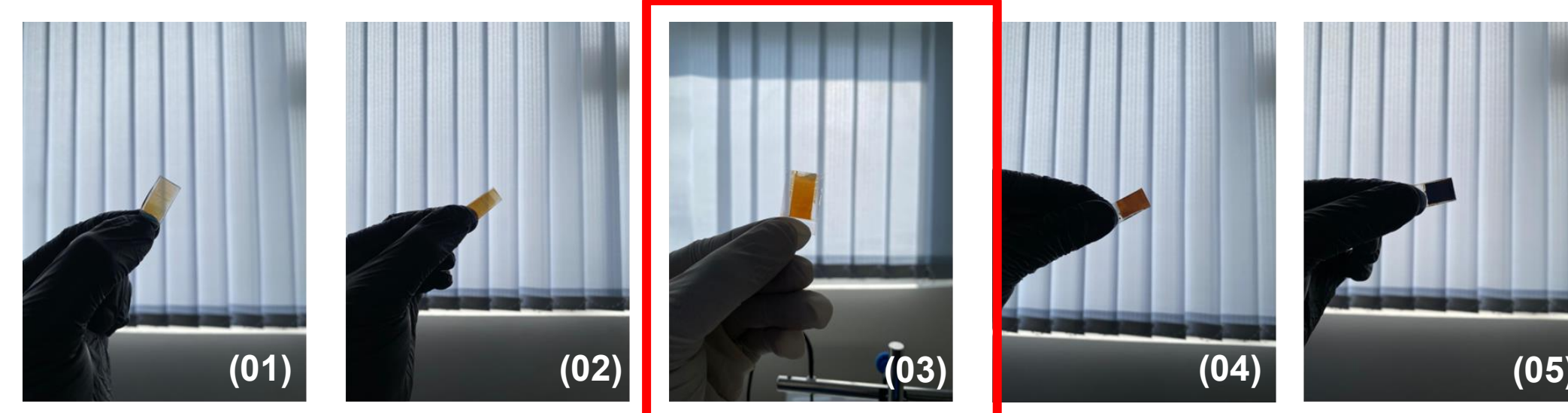


Figure 02 : Tested Dipping times of Solar Cells : (01) 1 hour , (02) 2 hours , (03) 3 hours (04) 4 hours , (05) 5 hours
FTO / TiO₂ / CuSbS₂

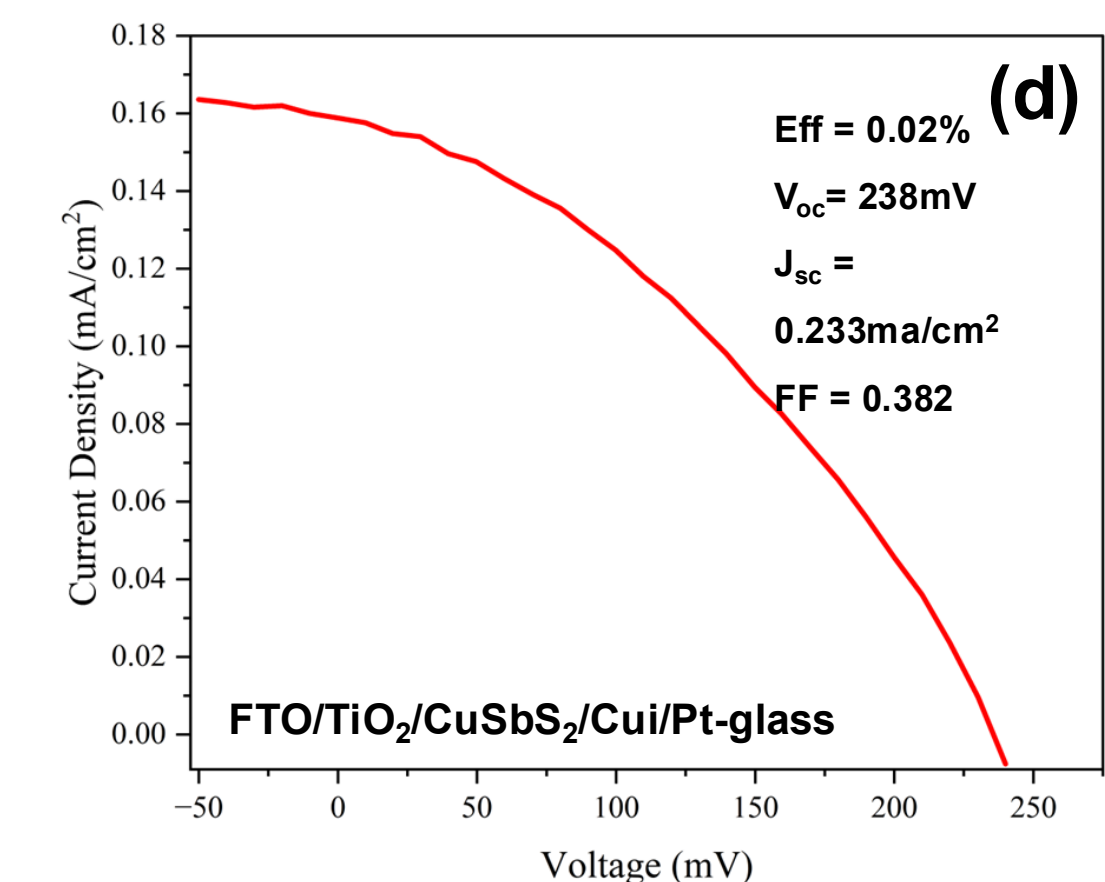
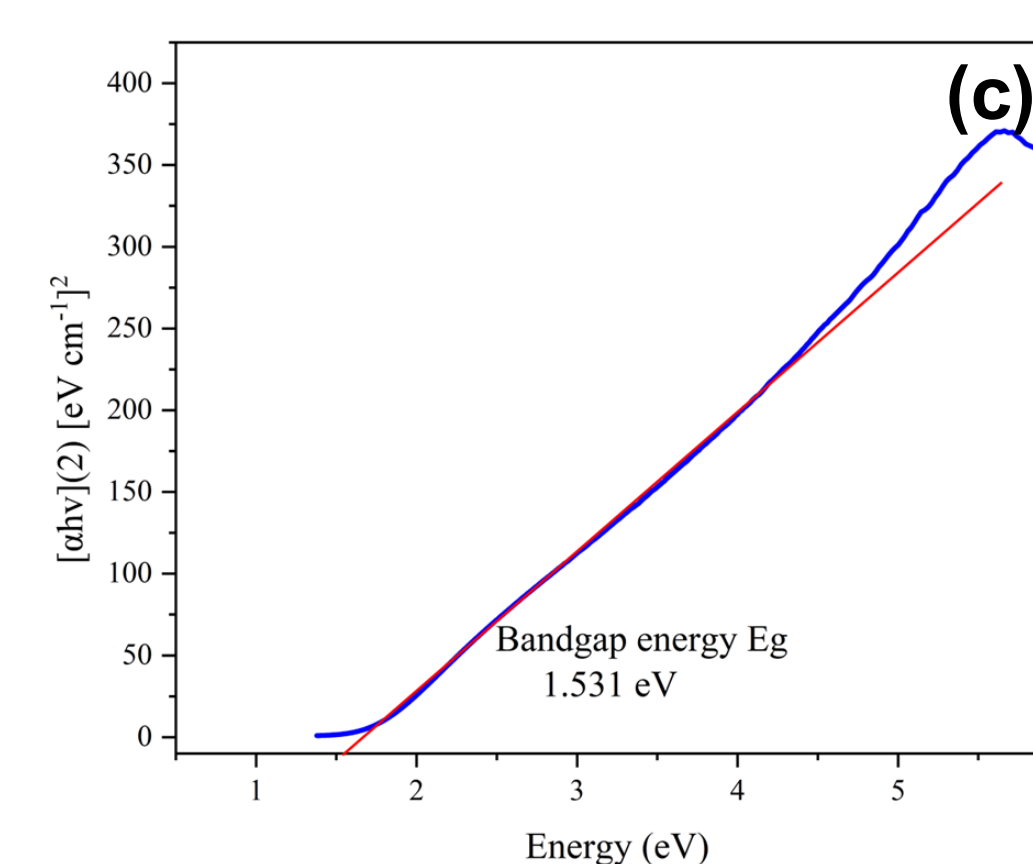
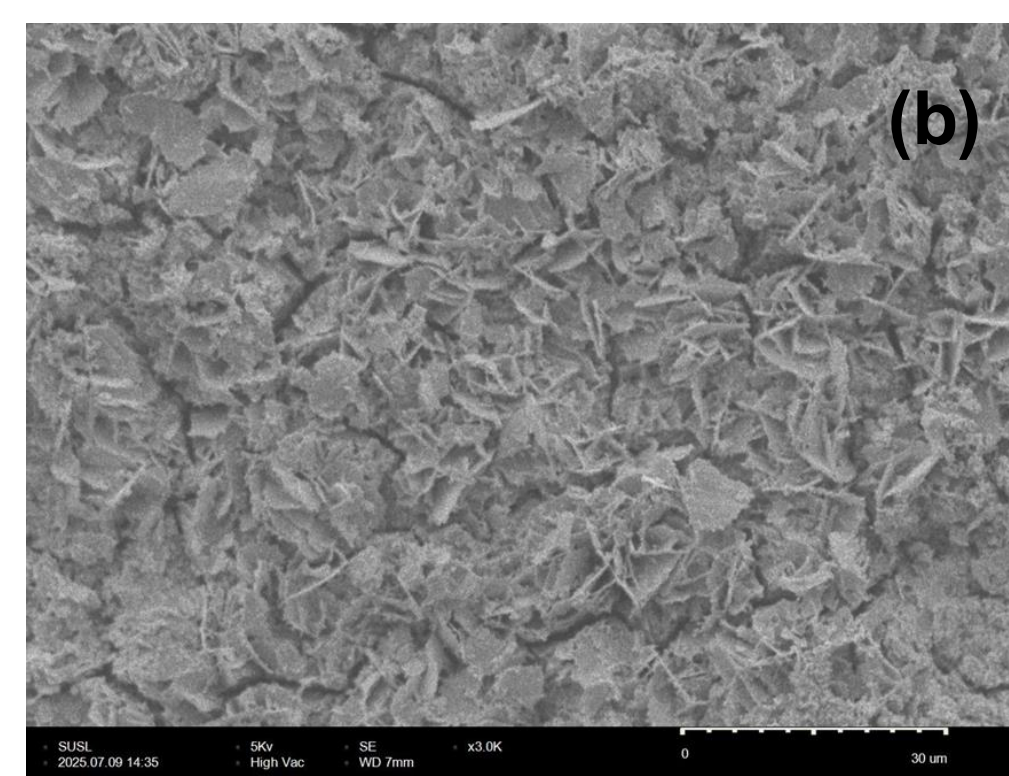
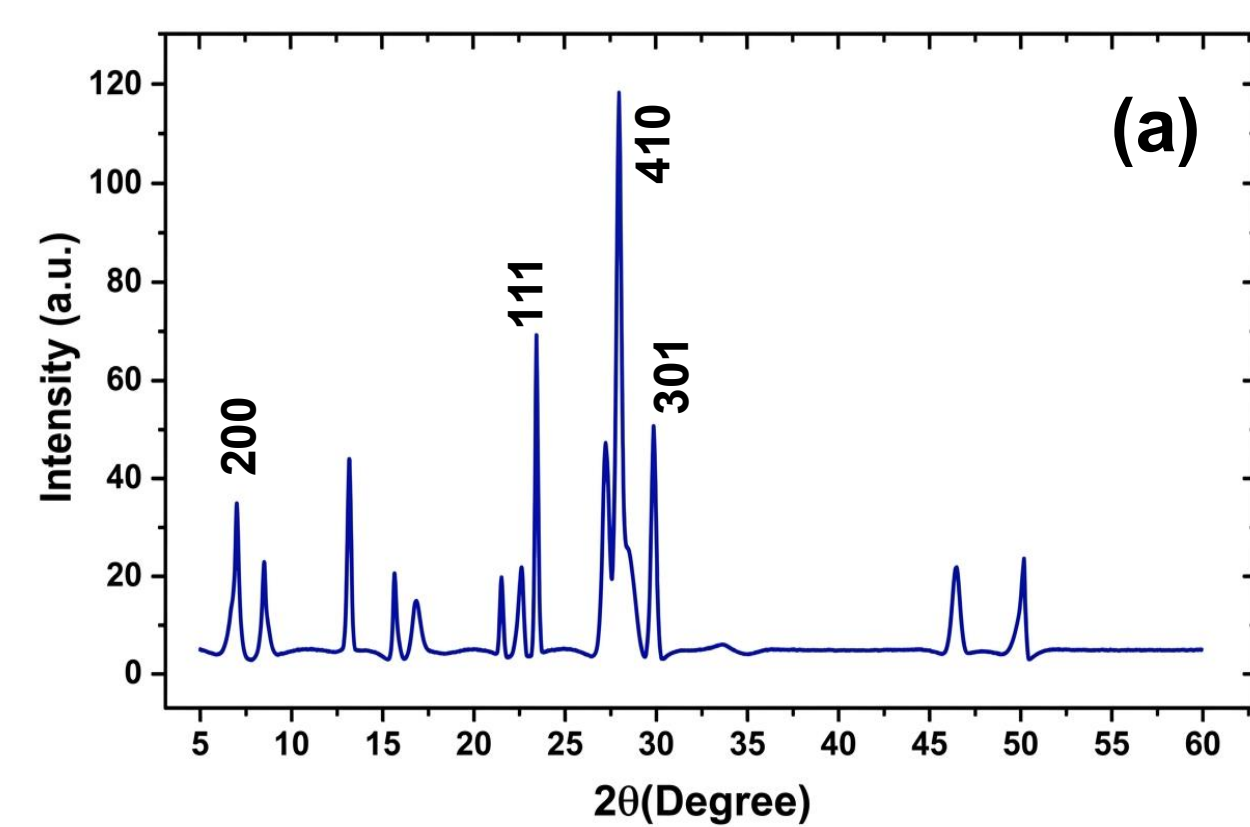


Table 01

Solar Cell	J _{sc} (mA cm ⁻²)	V _{oc}	FF	η (%)
(01)	0	0	0	0
(02)	0.017	0.100	0.265	4.5 x 10 ⁻⁴
(03)	0.168	0.247	0.398	169 x 10 ⁻⁴
(04)	0.016	0.042	0.260	1.72 x 10 ⁻⁴
(05)	0.002	0.001	0.130	2.6 x 10 ⁻⁷

Figure (a) shows the XRD pattern of the synthesized material, confirming its successful formation through well-defined peaks that match the standard JCPDS card. Figure (b) presents the SEM image of the thin film prepared by 3-hour dipping for the solar cell, clearly demonstrating uniform and successful coating of the film. Figure (c) displays the Tauc plot used to determine the optical bandgap of the material, calculated to be 1.53 eV. Figure (d) illustrates the current-voltage (I-V) characteristics of the optimized solar cell. Additionally, the Table 01 summarizes the overall photovoltaic performance parameters for devices fabricated at different dipping times.

CONCLUSIONS

- CuSbS₂ thin films were successfully deposited on FTO glass via optimized CBD method.
- XRD patterns show the orthorhombic structure films in polycrystalline nature.
- According to Tauc plots, optical band gaps of CuSbS₂ films are estimated to be 1.5 eV.
- The solar cell immersed for 3 hours exhibited the best photovoltaic performance.
- The best deposition time for the CuSbS₂ thin film is 3 h by the optimized chemical bath deposition method.

FUTURE WORKS

- Future research will focus on enhancing the efficiency of CuSbS₂ thin-film solar cells through systematic doping with d-block elements (Fe, Co, Ni, Mn).
- In addition to elemental doping, further studies will investigate interface engineering between the TiO₂ electron transport layer and the CuSbS₂ absorber layer to reduce charge recombination losses.

REFERENCES

- Macías, C. et al. (2017) "Thin film solar cell based on CuSbS₂ absorber prepared by chemical bath deposition (CBD)." *Materials Research Bulletin*, 87, 161–166
- Lin, W.W. et al. (2022) "A facile Ion-Exchange assisted chemical bath deposition of CuSbS₂ for thin film solar cells." *Solar Energy*, 244, 465–473.
- Chalapathi, U. et al. (2024) "CuSbS₂ thin films and solar cells produced from Cu/Sb stacked precursors via sulfurization." (with references to CBD routes). *Heliyon*.
- Valeti, N.J. et al. (2024) "Numerical investigation of CuSbS₂ thin film solar cell using SCAPS-1D." *Materials Research Express*